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## AlGaN/GaN HEMTs-an overview of device operation and applications

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965	Large-signal modeling up to W-band of AlGa <sub>N</sub> /Ga <sub>N</sub> based high-electron-mobility transistors. <b>2015</b> ,	2
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96	Performance improvement in AlGa <sub>N</sub> /Ga <sub>N</sub> high electron mobility transistors by low-temperature ICP-CVD SiN <sub>x</sub> as gate dielectric and surface passivation.	0
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